

APR-25-2003 FRI 10:17 AM

FAX NO.

P. 02

FAX RECEIVED

APR 26 2003

TECHNOLOGY CENTER 2800

#17/E

5-1-03

PATENT  
465-758P

**IN THE U.S. PATENT AND TRADEMARK OFFICE**

Applicant:	Jun S. LEE	Conf.:	5244
Serial No.:	09/722,583	Art Unit:	2823
Filed:	November 28, 2000	Examiner:	B. Kebede
For:	METHOD FOR FABRICATING CAPACITOR OF SEMICONDUCTOR DEVICE		

**SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111**

Assistant Commissioner for Patents  
Washington, DC 20231

February 5, 2003

Sir:

In response to the Office Action mailed November 7, 2002 (Paper No. 14), the following amendments and remarks are respectfully submitted in connection with the above-identified application:

**IN THE CLAIMS:**

Please **rewrite claims 1 and 4** as follows:

1. (Twice Amended) A method for fabricating a capacitor of a semiconductor device comprising:

depositing a nitride film and an oxide film over a substrate, the oxide film being deposited on the nitride film by chemical vapor deposition;

sequentially etching the oxide film and the nitride film using a patterned photoresist as a mask;